

85V N-Channel Enhancement Mode MOSFET

1.Product Information

1.1 Features

- ◇ Surface-mounted package
- ◇ Advanced SGT cell design

1.2 Applications

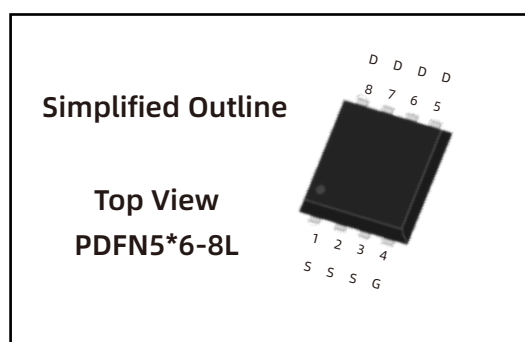
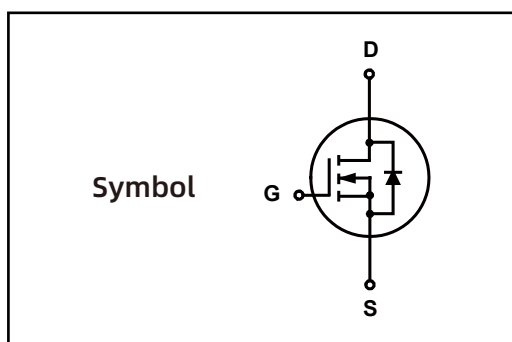
- ◇ LCD TV appliances
- ◇ LCDM appliances
- ◇ High power inverter system

1.3 Quick reference

- ◇ $BV \geq 85\text{ V}$
- ◇ $P_{\text{tot}} \leq 35\text{ W}$
- ◇ $I_D \leq 120\text{ A}$

- ◇ $R_{\text{DS(ON)}} \leq 5.5\text{ m}\Omega @ V_{\text{GS}} = 10\text{ V}$

2.Pin Description



3.Marking Information

Product Name	Marking
LN048N085G	LN048N085G CYWWZZ XXXXXX

4.Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C = 25\text{ }^{\circ}\text{C}$	85	-	V
V_{GS}	Gate-Source Voltage	$T_C = 25\text{ }^{\circ}\text{C}$	-	± 20	V
I_D^{***}	Drain Current (DC)	$T_C = 25\text{ }^{\circ}\text{C}, V_{GS} = 10\text{ V}$	-	120	A
		$T_C = 100\text{ }^{\circ}\text{C}, V_{GS} = 10\text{ V}$	-	65	A
$I_{DM}^{*,***}$	Drain Current (Pulsed)	$T_C = 25\text{ }^{\circ}\text{C}, V_{GS} = 10\text{ V}$	-	240	A
P_{tot}	Drain power dissipation	$T_C = 25\text{ }^{\circ}\text{C}$	-	156	W
T_{stg}	Storage Temperature		-55	150	$^{\circ}\text{C}$
T_J	Junction Temperature		-	150	$^{\circ}\text{C}$
I_S	Continuous-Source Current	$T_C = 25\text{ }^{\circ}\text{C}$	-	120	A
$R_{\theta JA}^{**}$	Thermal Resistance- Junction to Ambient		-	43	$^{\circ}\text{C/W}$
$R_{\theta JC}^{**}$			-	1.3	

Notes :

* Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

** Mounted on Large Heat Sink

*** limited by bonding wire

5.Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
LN048N085G	PDFN5*6	$\varnothing 330\text{mm}$	12mm	5000	

Note: COMTECH defines “ Green ” as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC / JEDEC J-STD-020C)

6. Electrical Characteristics ($T_A=25^\circ$ Unless Otherwise Noted)

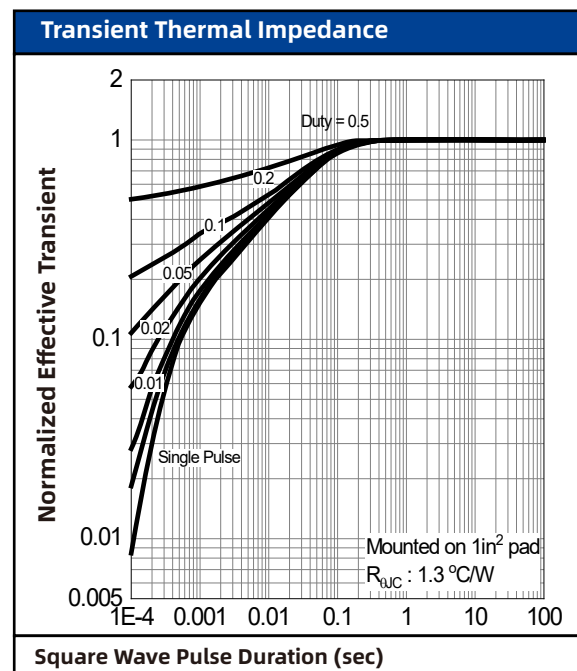
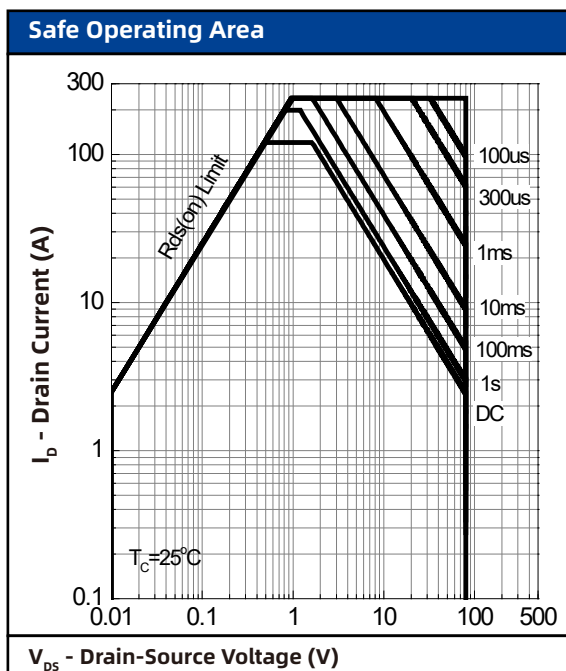
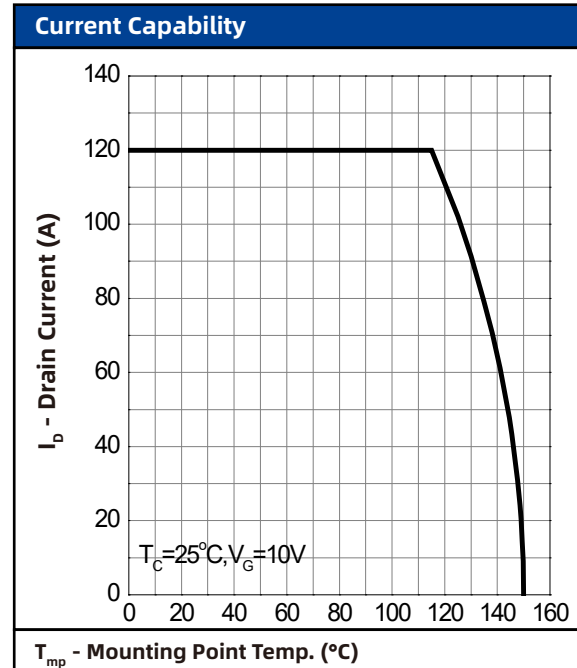
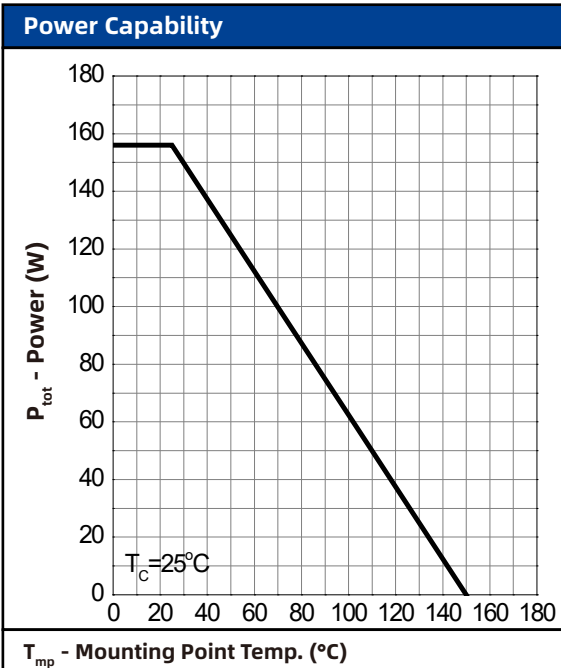
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _{DS} = 250 μA	85	95	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 0 V, I _{DS} = 250 μA	2.0	-	4.0	V
I _{DSS}	Drain Leakage Current	V _{DS} = 64 V, V _{GS} = 0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{DS} = 0 V, V _{GS} = ± 20 V	-	-	±100	nA
R _{DS(ON)} ^a	On-State Resistance	V _{GS} = 10 V, I _{DS} = 20 A	-	4.8	5.5	mΩ
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} = 20 A, V _{GS} = 0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{DS} = 20 A, V _{GS} = 0 V	-	76	-	nS
Q _{rr}	Reverse Recovery Charge	dI _{SD} /dt = 100 A/μs	-	125	-	nC
Dynamic Characteristics ^b						
C _{iSS}	Input Capacitance	V _{GS} = 0 V, V _{DS} = 40 V Frequency = 1 MHz	-	3562	-	pF
C _{oSS}	Output Capacitance		-	602	-	
C _{rSS}	Reverse Transfer Capacitance		-	34	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} = 40 V, V _{GEN} = 10 V, R _G = 4.5 Ω, R _L = 2 Ω, I _{DS} = 20 A	-	19	-	nS
t _r	Turn-on Rise Time		-	53	-	
t _{d(off)}	Turn-off Delay Time		-	52	-	
t _f	Turn-off Fall Time		-	55	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} = 40 V, V _{GS} = 10 V, I _{DS} = 20 A	-	83		nC
Q _{gs}	Gate-Source Charge		-	21		
Q _{gd}	Gate-Drain Charge		-	24		

Notes :

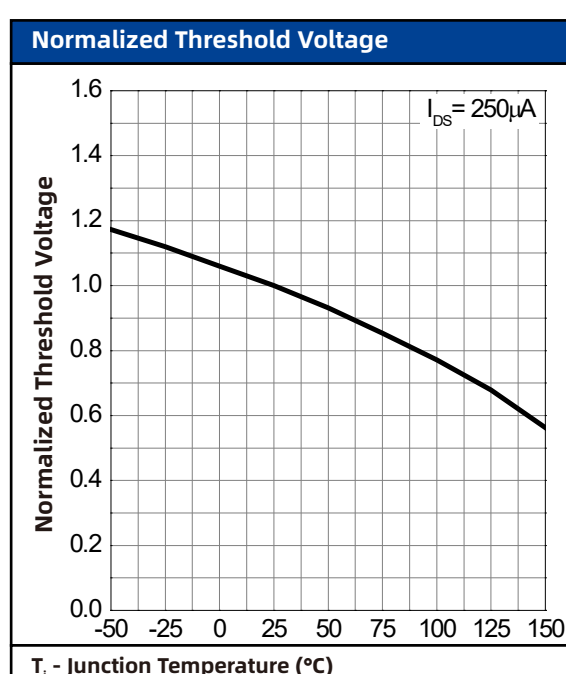
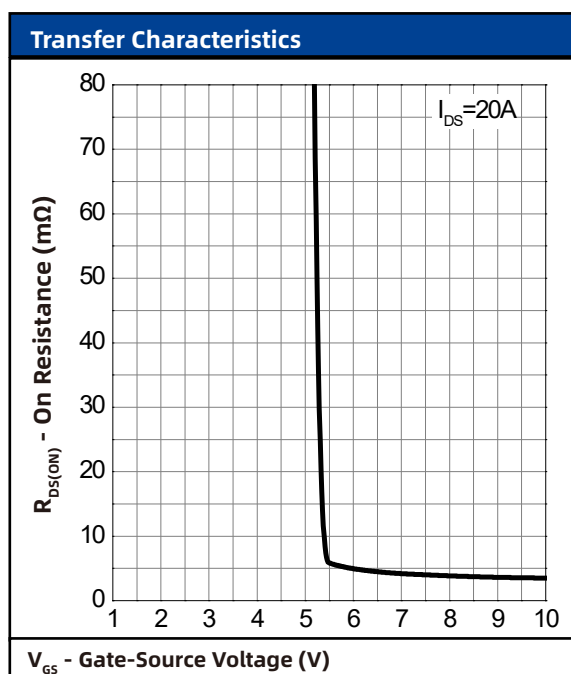
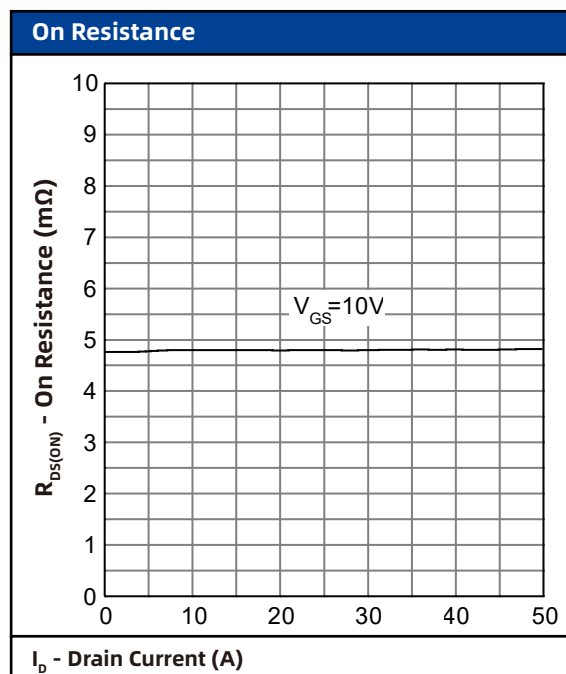
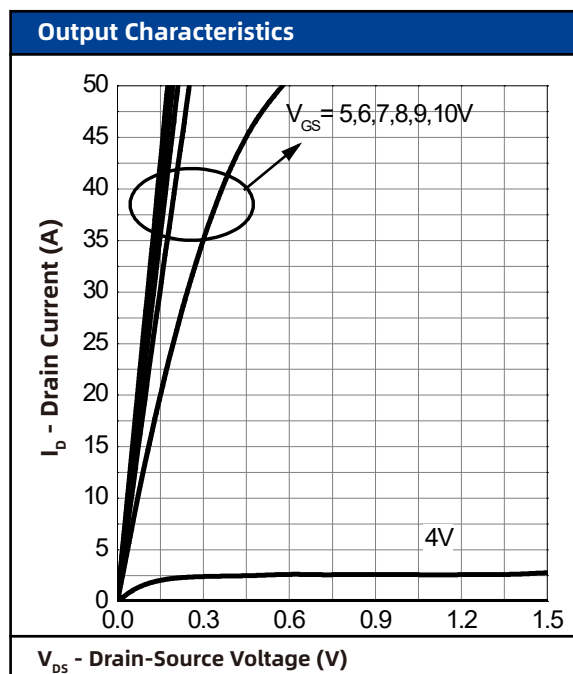
a : Pulse test ; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$

b : Guaranteed by design, not subject to production testing

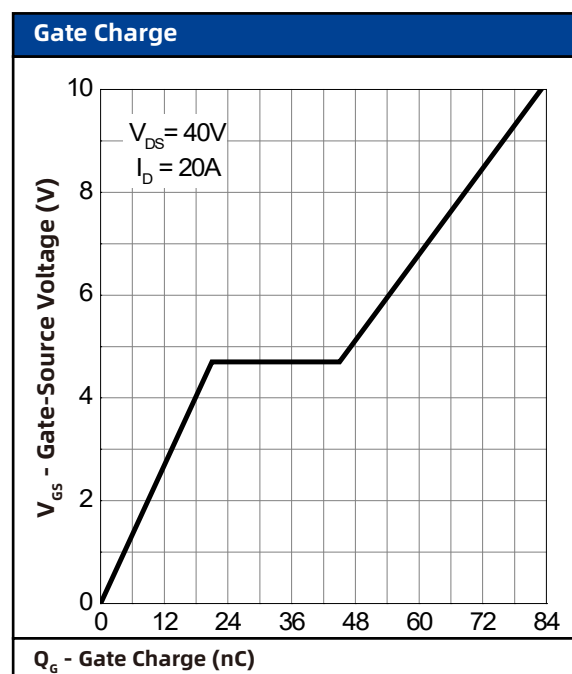
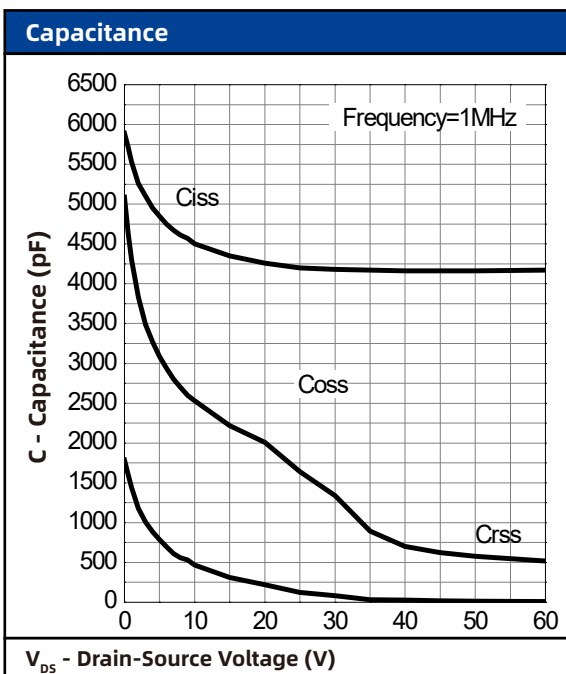
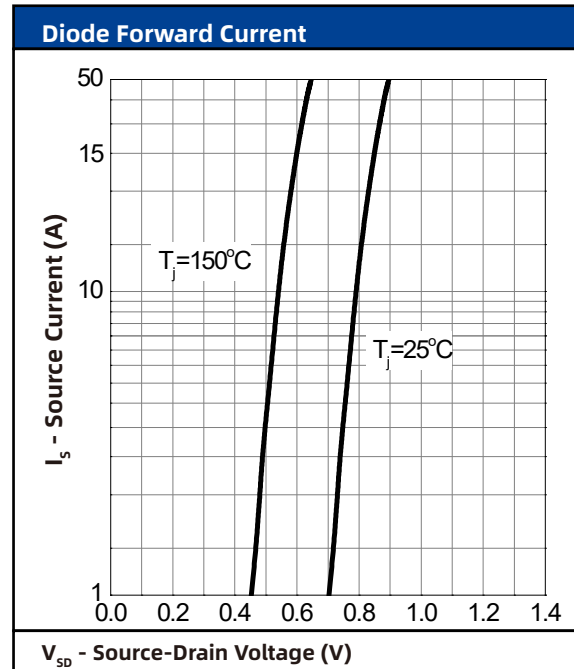
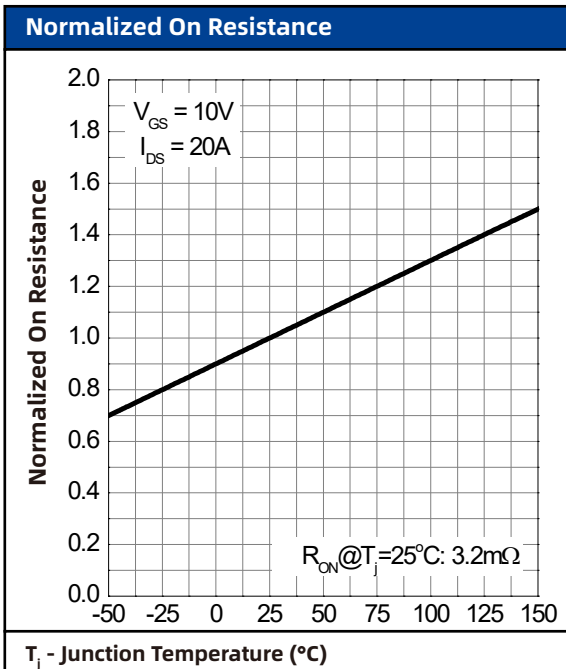
7. Typical Characteristics



7. Typical Characteristics (cont.)

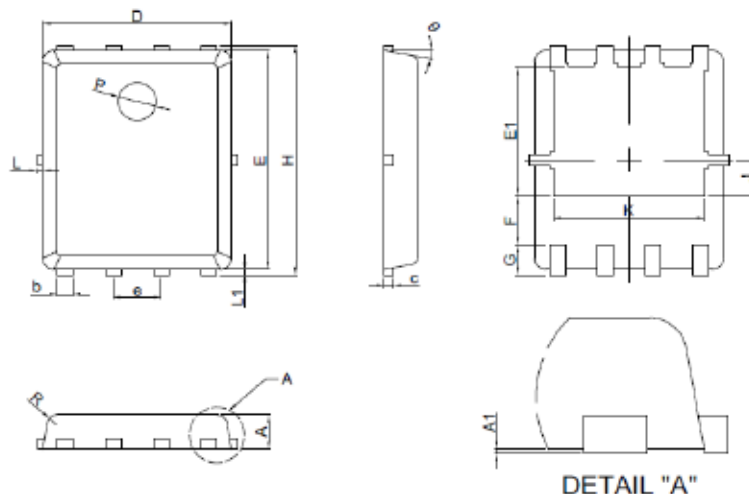


7. Typical Characteristics (cont.)



8. Package Dimensions

PDFN5*6-8L Package



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.80	1.00
A1	0.00	0.05
b	0.35	0.49
c	0.254REF	
D	4.90	5.10
F	1.40REF	
E	5.70	5.90
e	1.27BSC	
H	5.95	6.20
L1	0.10	0.18
G	0.60REF	
K	4.00REF	
L	-	0.15
J	0.95BSC	
P	1.00REF	
E1	3.40REF	
θ	6°	14°
R	0.25REF	